



PE2306A

N-Channel Enhancement Mode Power MOSFET

Description

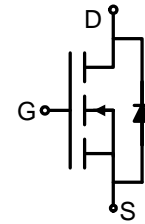
The PE2306A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with low gate voltage. This device is suitable for use as a battery protection or in other switching application.

General Features

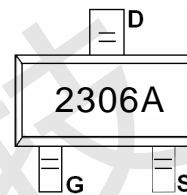
- $V_{DS} > 20V, I_D = 1.6A$
 $R_{DS(ON)} < 85m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 110m\Omega @ V_{GS}=2.5V$
- Surface Mount Package

Application

- Load/ power switching cell phones pagers
- Power supply converter circuits



Schematic diagram



Marking and pin assignment



SOT-23 top view

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------|------------|
| Drain-Source Voltage | V_{DS} | 20 | V |
| Gate-Source Voltage | V_{GS} | ± 10 | V |
| Drain Current-Continuous | I_D | 1.6 | A |
| Drain Current-Pulsed ^(Note 1) | I_{DM} | 3 | A |
| Maximum Power Dissipation | P_D | 0.75 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | $^\circ C$ |

Thermal Characteristic

| | | | |
|---|-----------------|-------|--------------|
| Thermal Resistance, Junction-to-Ambient ^(Note 2) | $R_{\theta JA}$ | 166.6 | $^\circ C/W$ |
|---|-----------------|-------|--------------|

Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|--------------------------------|------------|---------------------------|-----|-----|-----|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 20 | - | - | V |



PE2306A

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|--------------|--|-----|------|---------|------------|
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=20V, V_{GS}=0V$ | - | - | 100 | nA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 4.5V, V_{DS}=0V$ | - | - | ± 1 | μA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 0.5 | 0.75 | 1.2 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=4.5V, I_D=0.6A$ | - | 70 | 85 | m Ω |
| | | $V_{GS}=2.5V, I_D=0.3A$ | - | 90 | 110 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=10V, I_D=0.4A$ | - | 1 | - | S |
| Dynamic Characteristics (Note 4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0 V, f = 1.0 MHz,$ $V_{DS} = 10 V$ | - | 96 | - | pF |
| Output Capacitance | C_{oss} | | - | 18 | - | pF |
| Reverse Transfer Capacitance | C_{rss} | | - | 9 | - | pF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V = 10 V, R = 47\Omega$ $I_D = 200 mA,$ $V_{GEN} = 4.5 V, R_G = 10\Omega$ | - | 5 | - | nS |
| Turn-on Rise Time | t_r | | - | 5 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 25 | - | nS |
| Turn-Off Fall Time | t_f | | - | 11 | - | nS |
| Total Gate Charge | Q_g | $V_{DS} = 10 V, V_{GS} = 4.5 V,$ $I_D = 250 mA$ | - | 800 | - | pC |
| Gate-Source Charge | Q_{gs} | | - | 75 | - | pC |
| Gate-Drain Charge | Q_{gd} | | - | 225 | - | pC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V_{SD} | $V_{GS}=0V, I_S=0.2A$ | - | 0.75 | 1.2 | V |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

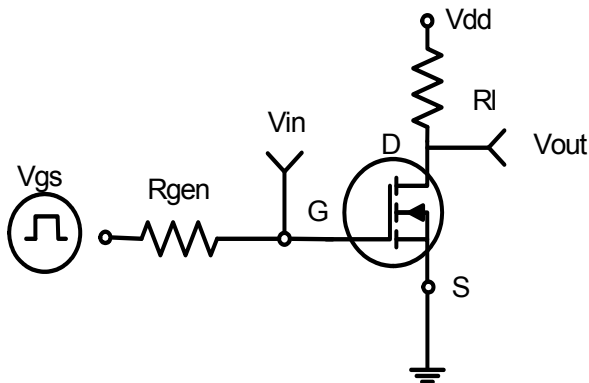


Figure 1: Switching Test Circuit

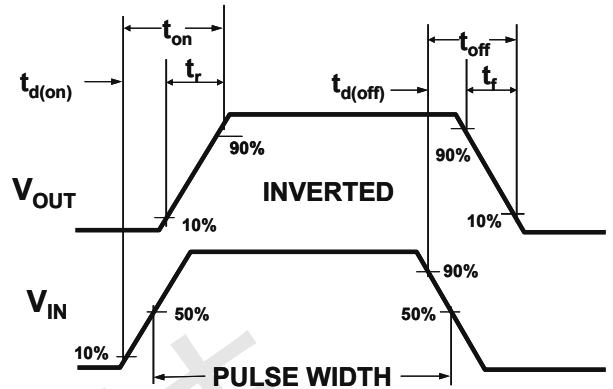


Figure 2: Switching Waveforms

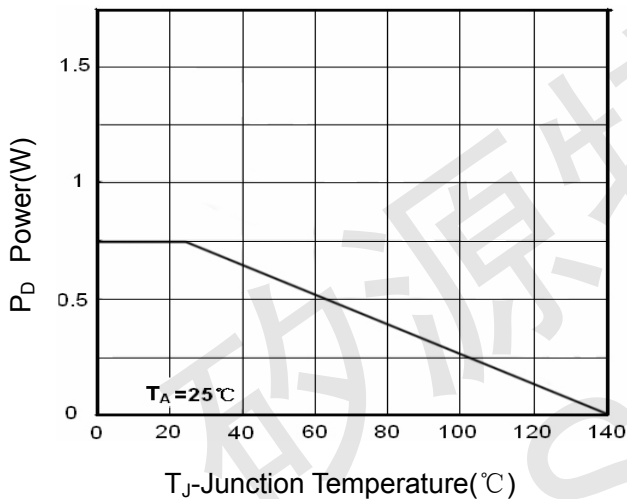


Figure 3 Power Dissipation

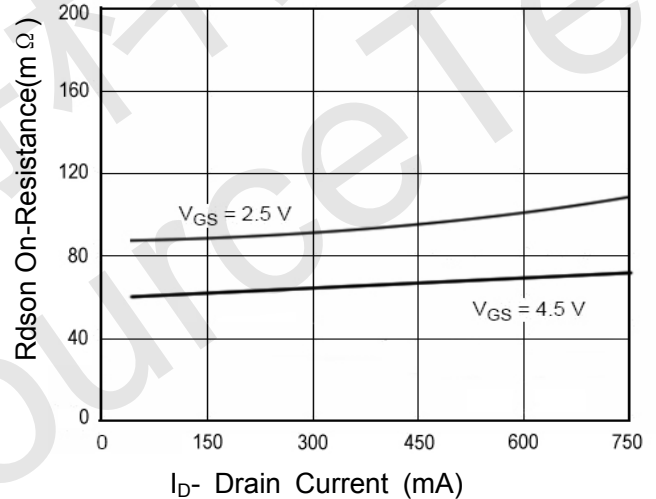


Figure 6 Drain-Source On-Resistance

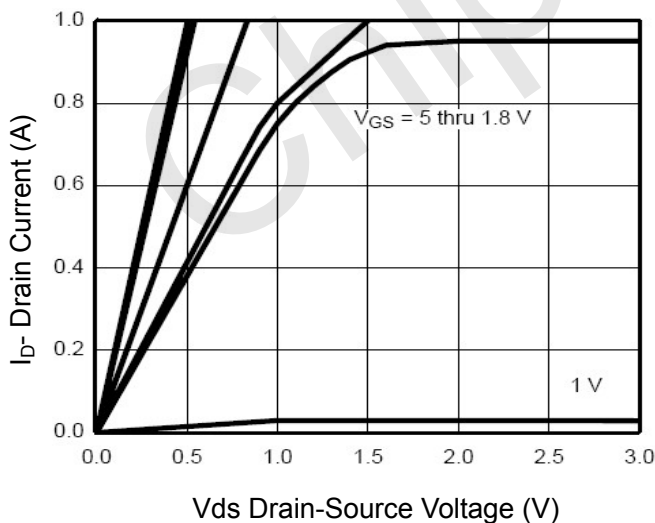


Figure 5 Output Characteristics

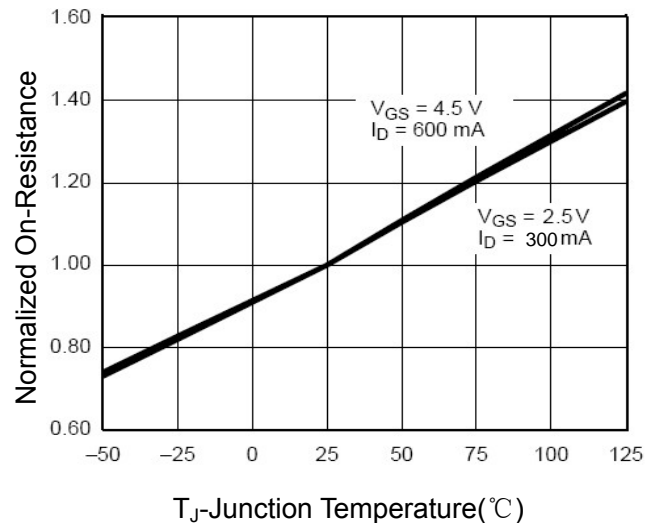
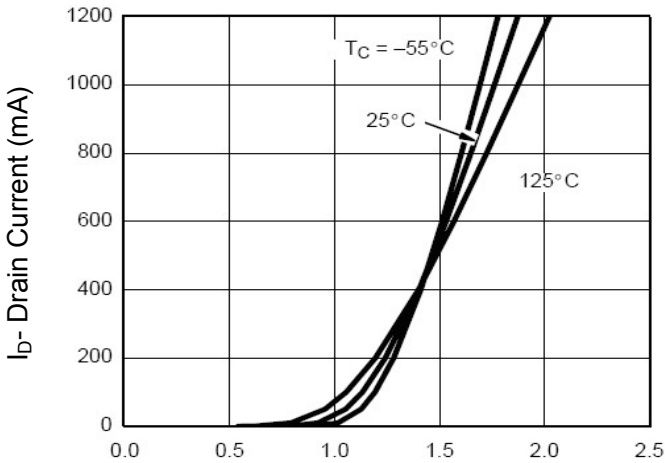


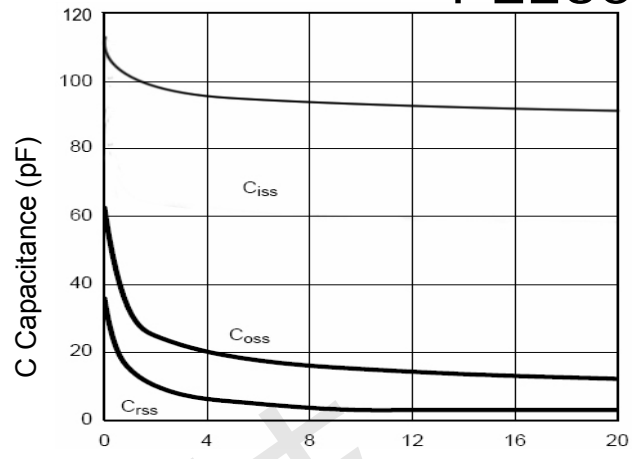
Figure 8 Drain-Source On-Resistance



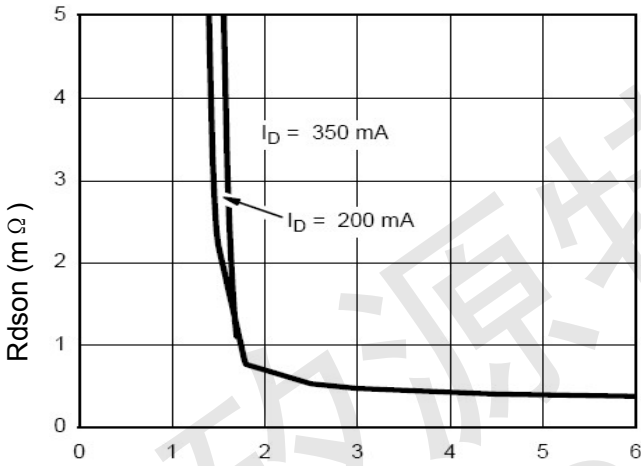
PE2306A



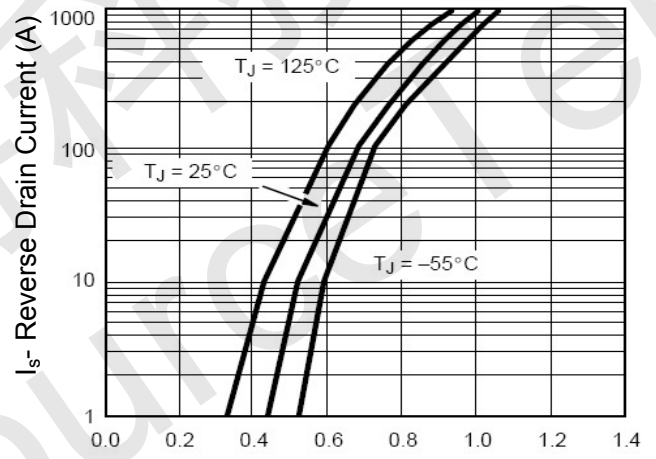
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



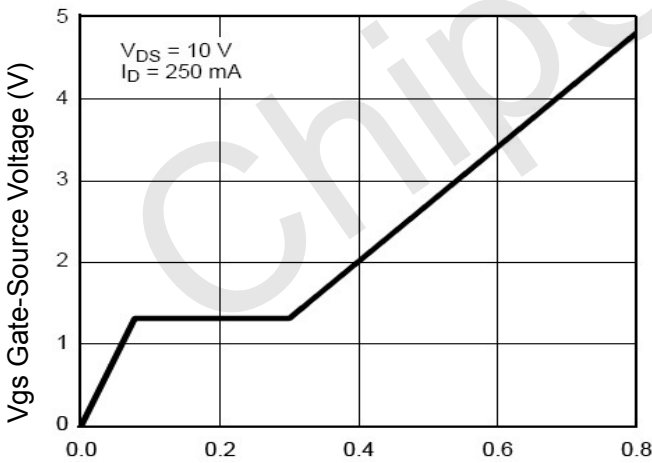
Vds Drain-Source Voltage (V)
Figure 8 Capacitance vs Vds



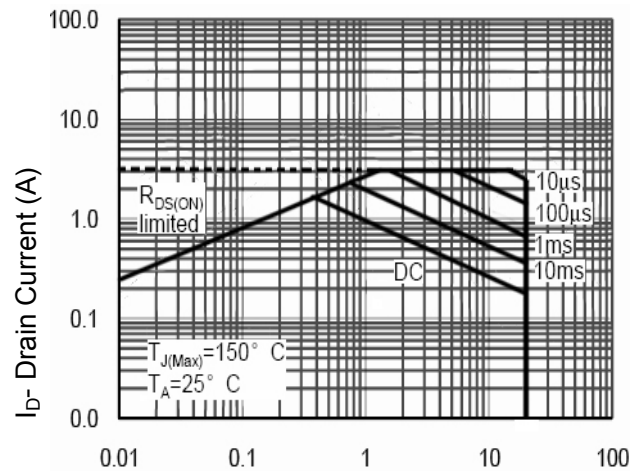
Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 11 Gate Charge



Vds Drain-Source Voltage (V)
Figure 13 Safe Operation Area

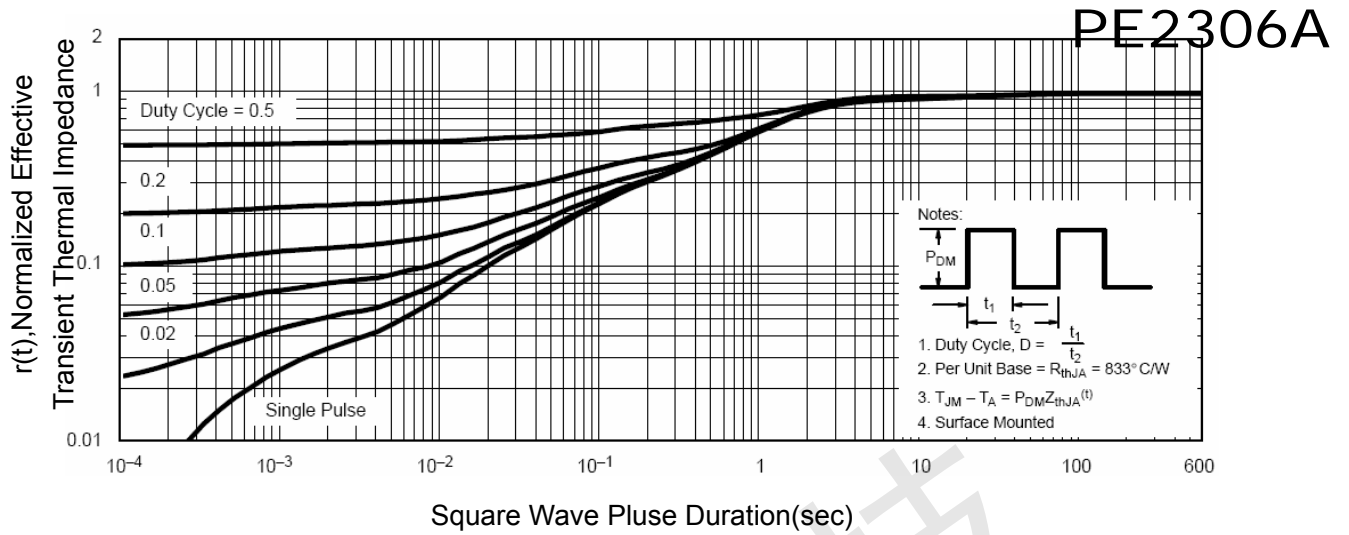


Figure 14 Normalized Maximum Transient Thermal Impedance

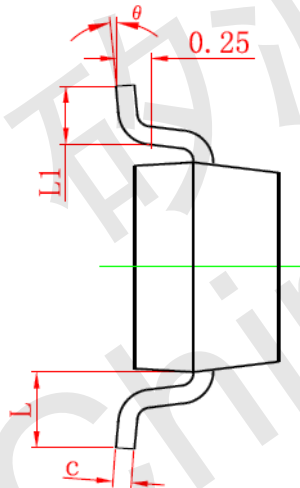
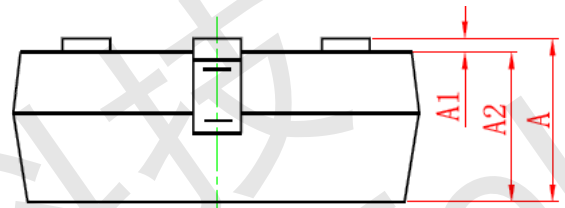
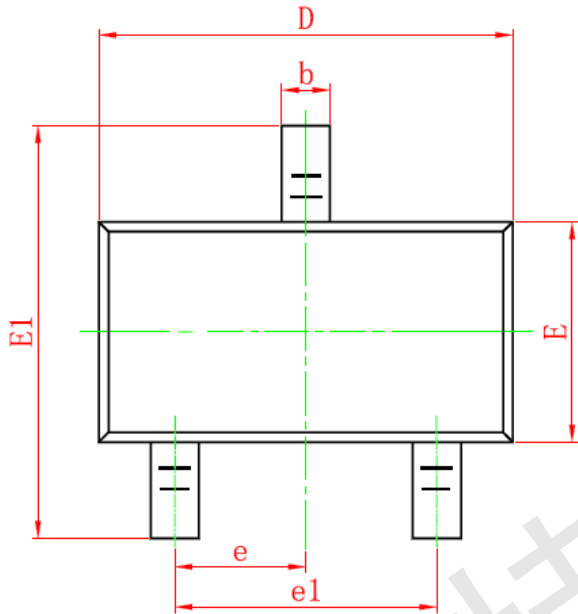
矽源特科技
ChipSourceTek



PE2306A

SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)



| Symbol | Dimensions in Millimeters | |
|--------|---------------------------|-------|
| | MIN. | MAX. |
| A | 0.900 | 1.150 |
| A1 | 0.000 | 0.100 |
| A2 | 0.900 | 1.050 |
| b | 0.300 | 0.500 |
| c | 0.080 | 0.150 |
| D | 2.800 | 3.000 |
| E | 1.200 | 1.400 |
| E1 | 2.250 | 2.550 |
| e | 0.950TYP | |
| e1 | 1.800 | 2.000 |
| L | 0.550REF | |
| L1 | 0.300 | 0.500 |
| θ | 0° | 8° |